



Unlocking the Mystery of Precision Inductors in High Volume Production RF Test Environments

Roger Hayward

Cascade Microtech, Inc.

As consumer wireless devices continue to become an everyday part of our lives, the silicon to drive these devices increase in complexity, and levels of integration. Frequency synthesizers provide tuning capability at some intermediate frequency, often above the actual carrier frequency. Buried behind the glamour of the Phase Lock Loop circuitry hides a lonely oscillator, starved for current and real estate, neglected and nearly forgotten.

Oscillators provide the heartbeat of the entire system. Without oscillation, nearly no sub-systems of the transceiver can be tested. The typical oscillator consists of a fixed inductor, and a variable capacitor. The capacitor provides the tuning, and thus phase-lock to a reference oscillator. The inductor's value, as small as it is, may consume too much real-estate on the die. Designers opt for moving this component into the die-package.

This presents an interesting challenge during KGD RF test. The probe must provide an inductance to the die which mimic's the die-package inductor. In many cases, the greater challenge is the inductor Q, not its inductance. With decreasing bias current in the FET, the demand on Q increases. Limited Q, and probing contact resistance may compromise the circuit's ability to oscillate.

This poster unlocks the mystery of when inductor Q is a bona-fide probing issue, and when it is not. In many cases, Q may be dismissed through correlating measurement data against sample data. In other cases where the demands on Q are justified, the designer may need to consider design-fortest (DFT) options within the oscillator circuitry.

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Emulating Lead Inductance





IEEE SW Test Workshop Semiconductor Wafer Test Workshop

Inductor Trimming for Phase Lock Loop Circuits



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Overcoming Inductor Q during KGD Test



	Known Good Die VCO / PLL "Design For Test."
Inductor Q is defined by: $Q = \frac{X_{L}}{R}$ A "High Q" inductor is built by achieving the inductance value with the minimum amount of passive loss. This is usually achieved by winding the line around ferromagnetic	Range of Oscillation with varying Bias Current
material. Within the thin film probe, Q is compromised by the lack of ferromagnetic material, and a small amount of contact resistance during probing.	5.5 5.5 5.5 5.5 5.5 5.5 5.5 5.5

Digital circuitry frequently contains extra devices, aimed specifically for the test phase of the device. These extra devices are never enabled after test. Still though, they serve a vital role at wafer sort.

High volume RF devices (such as cellular handset devices) run with the least amount of bias current possible (to extend battery life). To achieve this, the Q of the packaged device inductor must be high. During probing, sometimes this high Q cannot be achieved reliably.

By adding additional bias current to the oscillator, the limited Q can be overcome. This will increase output power of the oscillator, correct its frequency sweep range, and enable the rest of the device to be tested.

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